

89 [0056]

## ABSTRACT OF THE DISCLOSURE

90 [0057] Disclosed is a method of forming a thick silicon oxide layer upon or  
91 internal to a silicon structure. The method is particularly useful in creating isolation  
92 regions within a silicon-containing structure, where such isolation regions can withstand  
93 high voltages. The electrically isolating thick silicon oxide layer or isolation regions can  
94 be shaped, machined, or etched to provide feedthroughs for vertical or horizontal  
95 interconnects. The feedthroughs may be coated with metal or filled with metal to  
96 provide the interconnect.